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computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

10. A semiconductor device according to claim 9, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

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11. A semiconductor device according to claim 9, wherein said second electrode is a pixel electrode.

12. A semiconductor device according to claim 9, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

14. A semiconductor device according to claim 13, further comprising a liquid crystal layer provided over said second electrode.

15. A semiconductor device according to claim 13, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

16. A semiconductor device according to claim 13, wherein said second electrode is a pixel electrode.

17. A semiconductor device according to claim 13, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

18. A semiconductor device comprising:
a semiconductor film;

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a gate insulating film provided on said semiconductor film;
a first electrode which is provided on said gate insulating film and overlaps said semiconductor film;
an insulating film formed on said first electrode;
a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;
a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole; and
a second electrode provided on said insulating film,
wherein a storage capacitor is constructed by said first electrode, said gate insulating film, and said semiconductor film and overlapped at 90% or more of an area thereof with said second electrode.

19. A semiconductor device according to claim 18, further comprising a liquid crystal layer provided over said second electrode.

20. A semiconductor device according to claim 18, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

21. A semiconductor device according to claim 18, wherein said second electrode is a pixel electrode.

22. A semiconductor device according to claim 18, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

23. A semiconductor device comprising:
a first semiconductor film;
a second semiconductor film;

a gate insulating film provided on said first semiconductor film and said second semiconductor film;

a first electrode which is provided on said gate insulating film, intersects said first semiconductor film, and overlaps said second semiconductor film;

an insulating film formed on said first electrode;

a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;

a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole; and

a second electrode provided on said insulating film,

wherein a storage capacitor is constructed by said first electrode, said gate insulating film, and said second semiconductor film and overlapped at 90% or more of an area thereof with said second electrode.

24. A semiconductor device according to claim 23, further comprising a liquid crystal layer provided over said second electrode.

25. A semiconductor device according to claim 23, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

26. A semiconductor device according to claim 23, wherein said second electrode is a pixel electrode.

27. A semiconductor device according to claim 23, wherein said semiconductor device is incorporated into electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

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